

| | Document ID | Issue Date | Pages | Title | Current OR | Current XRef | Inventor |
|---|---------------|------------|-------|---|------------|----------------------|-------------------------|
| 1 | US 5665620 A | 19970909 | 8 | Method for forming concurrent top oxides using reoxidized silicon in an EEPROM | 438/593 | 438/265; 438/266; | Nguyen, Bich-Yen et al. |
| 2 | US 6319775 B1 | 20011120 | 7 | Nitridation process for fabricating an ONO floating-gate electrode in a two-bit EEPROM device | 438/261 | 438/594 | Halliyal, Arvind et al. |
| 3 | US 6180538 B1 | 20010130 | 7 | Process for fabricating an ONO floating-gate electrode in a two-bit EEPROM device using rapid-thermal-chemical-vapor-deposition | 438/769 | 438/786 | Halliyal, Arvind et al. |
| 4 | US 5856223 A | 19990105 | 11 | Method for manufacturing self-aligned split-gate flash memory cells | 438/264 | 438/266 | Wang, Lin-Song |